

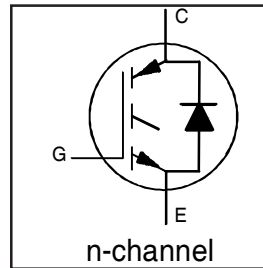
IRG4BC30UDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
 ULTRAFast SOFT RECOVERY DIODE

UltraFast CoPack IGBT

Features

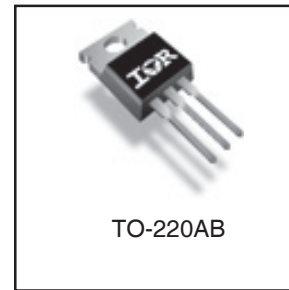
- UltraFast: Optimized for high operating frequencies 8-40 kHz in hard switching, >200 kHz in resonant mode
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on) typ.} = 1.95V$
@ $V_{GE} = 15V, I_C = 12A$

Benefits

- Generation -4 IGBT's offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs . Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	23	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	12	
I_{CM}	Pulsed Collector Current ①	92	
I_{LM}	Clamped Inductive Load Current ②	92	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	12	
I_{FM}	Diode Maximum Forward Current	92	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	°C
T_{STG}			
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	-----	-----	1.2	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	-----	-----	2.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	-----	0.50	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	80	
Wt	Weight	-----	2 (0.07)	-----	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	600	----	----	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	----	0.63	----	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	----	1.95	2.1	V	I _C = 12A
		----	2.52	----		I _C = 23A
		----	2.09	----		I _C = 12A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.0	----	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	----	-11	----	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ^④	3.1	8.6	----	S	V _{CE} = 100V, I _C = 12A
I _{CES}	Zero Gate Voltage Collector Current	----	----	250	μA	V _{GE} = 0V, V _{CE} = 600V
		----	----	2500		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
V _{FM}	Diode Forward Voltage Drop	----	1.4	1.7	V	I _C = 12A
		----	1.3	1.6		I _C = 12A, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	----	----	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions		
Q _g	Total Gate Charge (turn-on)	----	50	75		I _C = 12A		
Q _{ge}	Gate - Emitter Charge (turn-on)	----	8.1	12	nC	V _{CC} = 400V		
Q _{gc}	Gate - Collector Charge (turn-on)	----	18	27		V _{GE} = 15V		
t _{d(on)}	Turn-On Delay Time	----	40	----		T _J = 25°C		
t _r	Rise Time	----	21	----	ns	I _C = 12A, V _{CC} = 480V		
t _{d(off)}	Turn-Off Delay Time	----	91	140		V _{GE} = 15V, R _G = 23Ω		
t _f	Fall Time	----	80	130		Energy losses include "tail" and diode reverse recovery.		
E _{on}	Turn-On Switching Loss	----	0.38	----		mJ	See Fig. 9, 10, 11, 18	
E _{off}	Turn-Off Switching Loss	----	0.16	----				
E _{ts}	Total Switching Loss	----	0.54	0.9				
t _{d(on)}	Turn-On Delay Time	----	40	----		ns	T _J = 150°C, See Fig. 9, 10, 11, 18	
t _r	Rise Time	----	22	----			I _C = 12A, V _{CC} = 480V	
t _{d(off)}	Turn-Off Delay Time	----	120	----			V _{GE} = 15V, R _G = 23Ω	
t _f	Fall Time	----	180	----			Energy losses include "tail" and diode reverse recovery.	
E _{ts}	Total Switching Loss	----	0.89	----	mJ		Measured 5mm from package	
L _E	Internal Emitter Inductance	----	7.5	----				
C _{ies}	Input Capacitance	----	1100	----	pF		V _{GE} = 0V	
C _{oes}	Output Capacitance	----	73	----			V _{CC} = 30V	
C _{res}	Reverse Transfer Capacitance	----	14	----			f = 1.0MHz	
t _{rr}	Diode Reverse Recovery Time	----	42	60	ns		T _J = 25°C See Fig.	
I _{rr}	Diode Peak Reverse Recovery Current	----	80	120		T _J = 125°C 14	I _F = 12A	
		----	3.5	6.0		T _J = 25°C See Fig.		
Q _{rr}	Diode Reverse Recovery Charge	----	5.6	10		T _J = 125°C 15		V _R = 200V
		----	80	180		T _J = 25°C See Fig.		
di _(rec) M/dt	Diode Peak Rate of Fall of Recovery During t _b	----	220	600	T _J = 125°C 16	di/dt 200A/μs		
		----	180	----	T _J = 25°C See Fig.			
		----	120	----	T _J = 125°C 17			

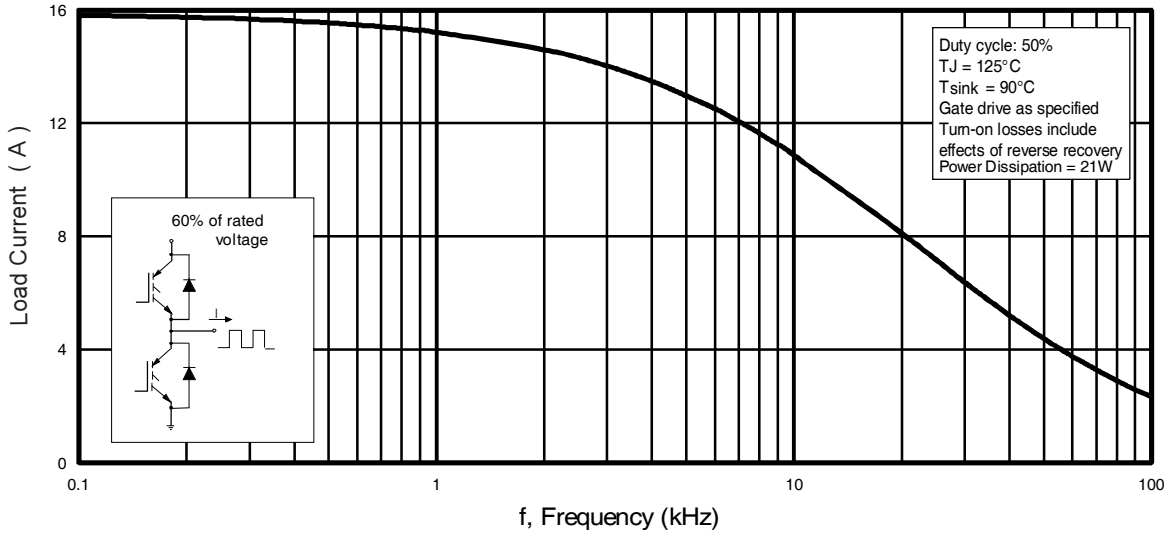


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

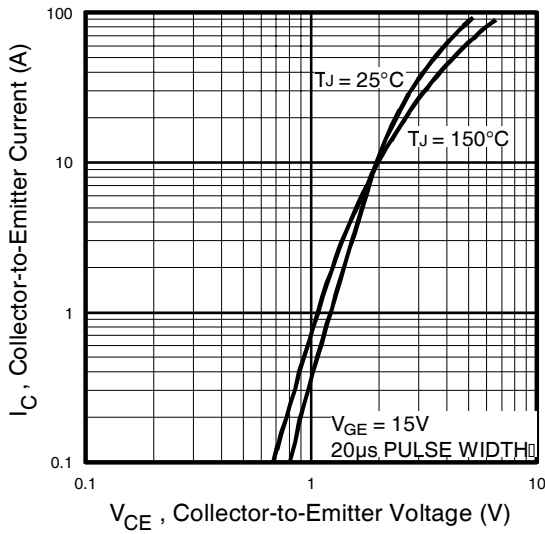


Fig. 2 - Typical Output Characteristics

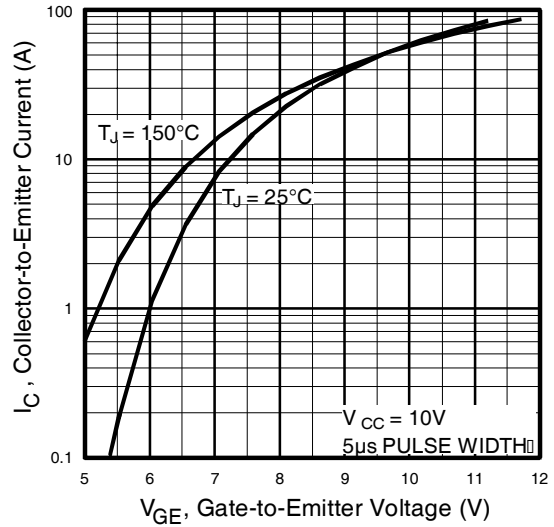


Fig. 3 - Typical Transfer Characteristics

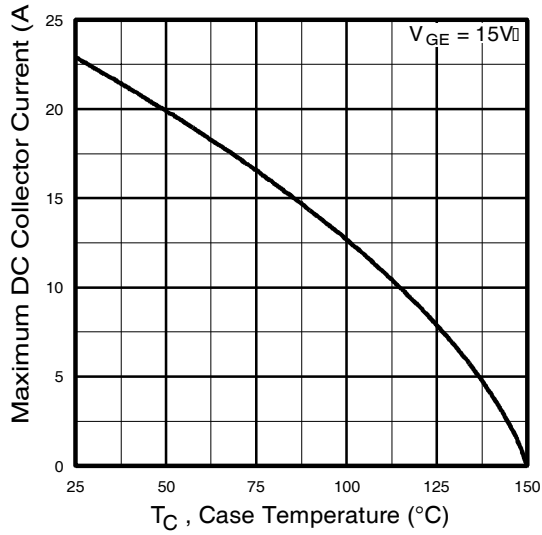


Fig. 4 - Maximum Collector Current vs. Case Temperature

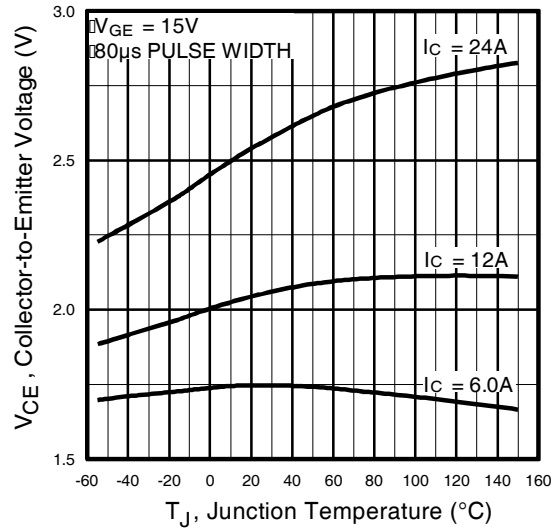


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

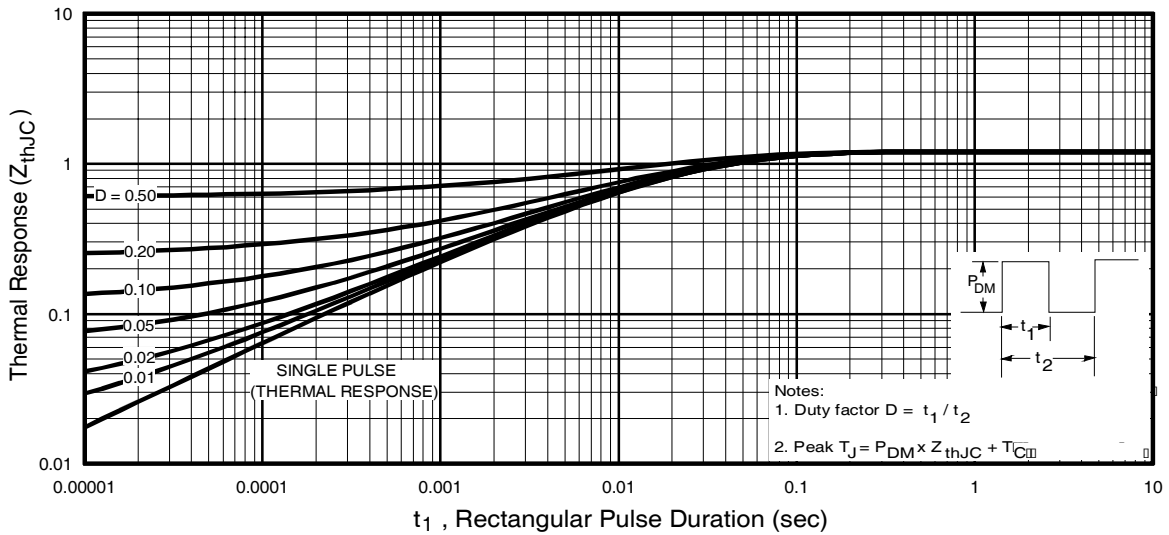


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

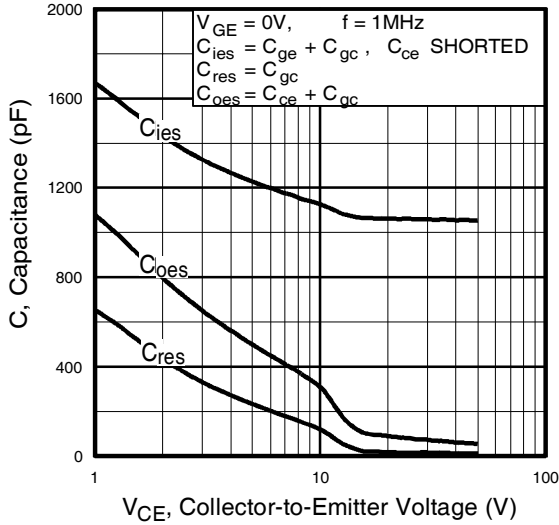


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

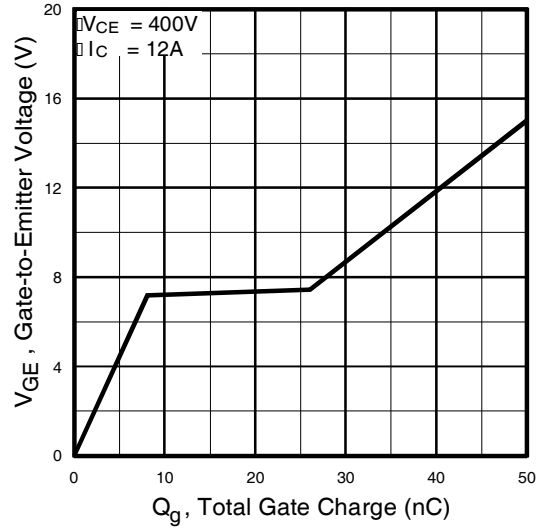


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

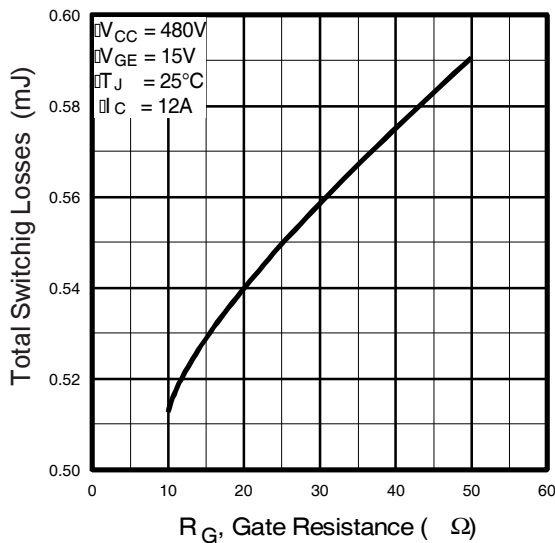


Fig. 9 - Typical Switching Losses vs. Gate Resistance

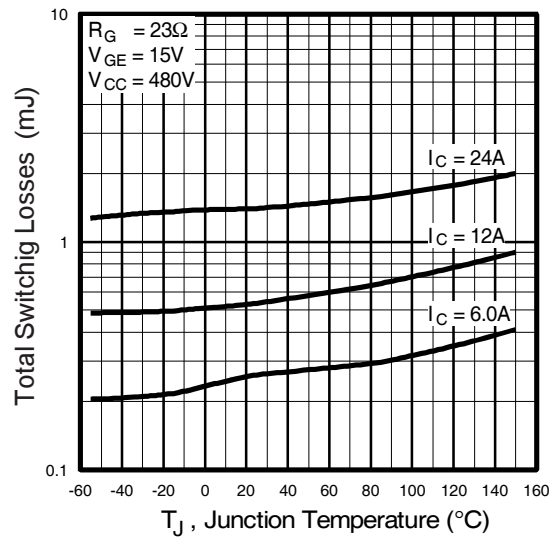


Fig. 10 - Typical Switching Losses vs. Junction Temperature

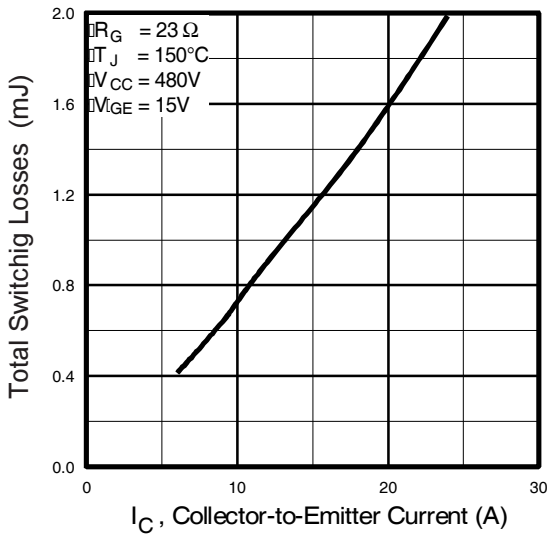


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

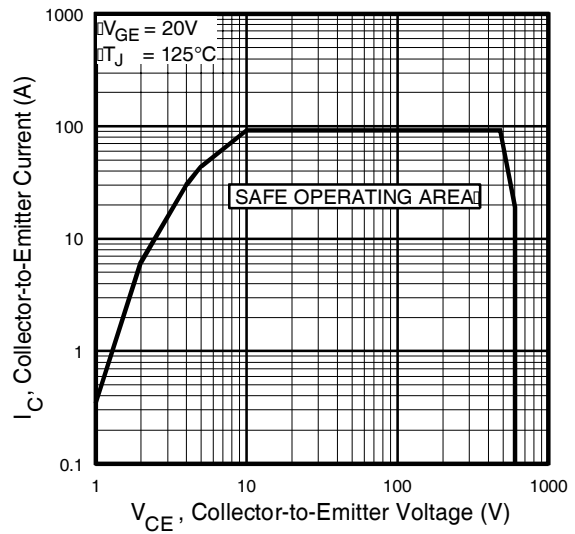


Fig. 12 - Turn-Off SOA

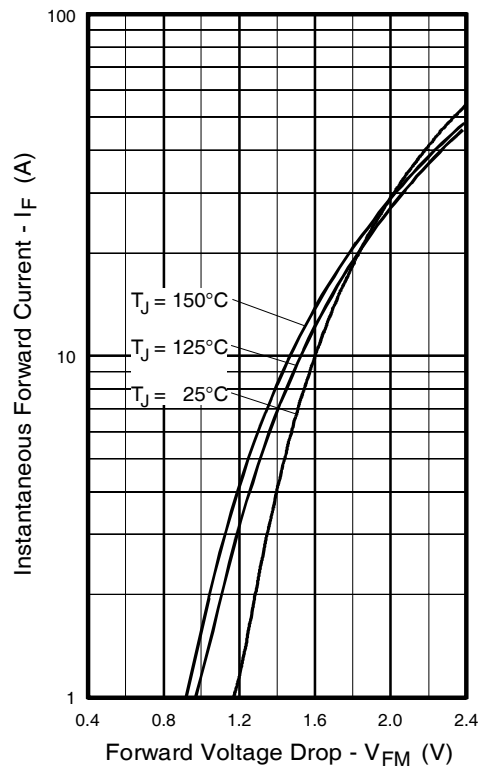


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

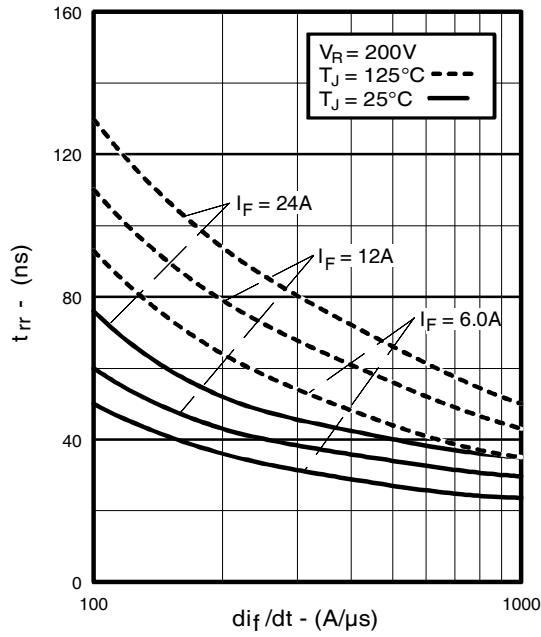


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

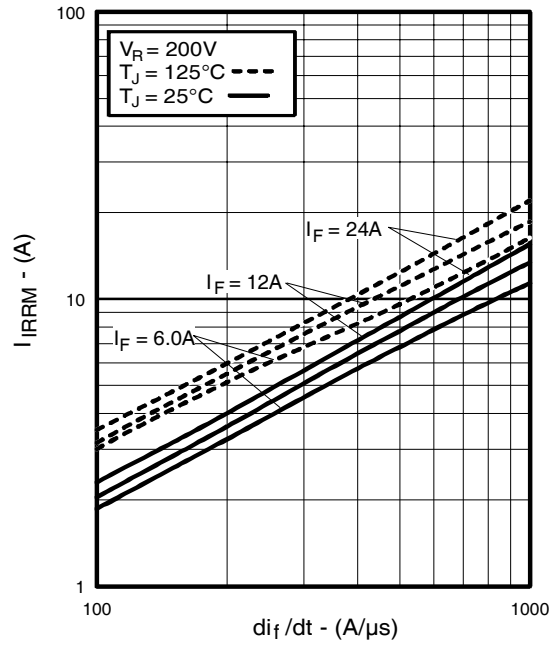


Fig. 15 - Typical Recovery Current vs. di_f/dt

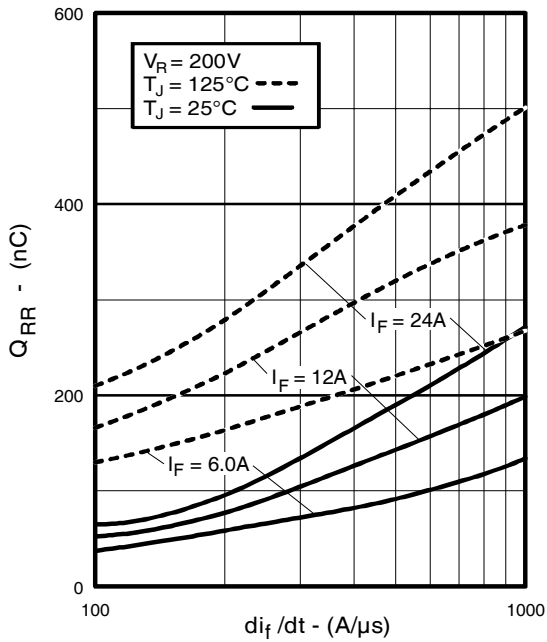


Fig. 16 - Typical Stored Charge vs. di_f/dt

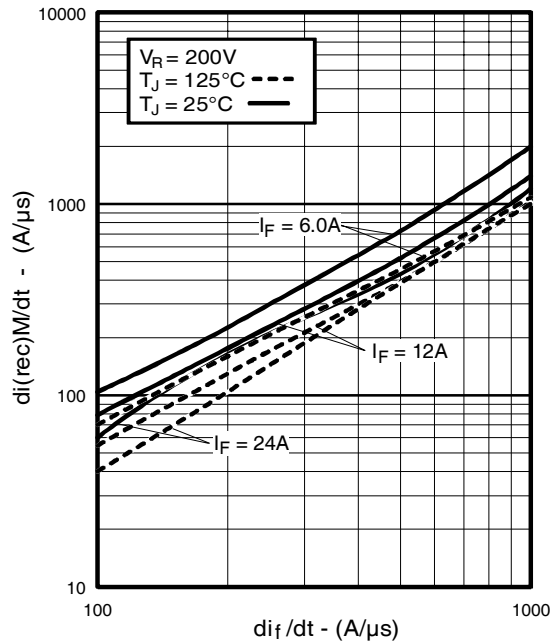


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

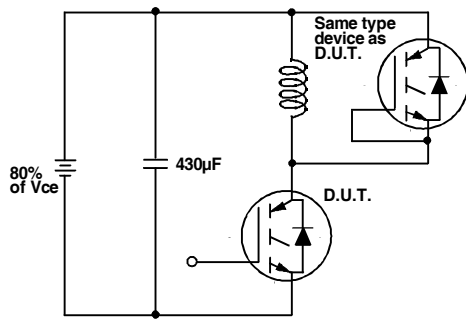


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

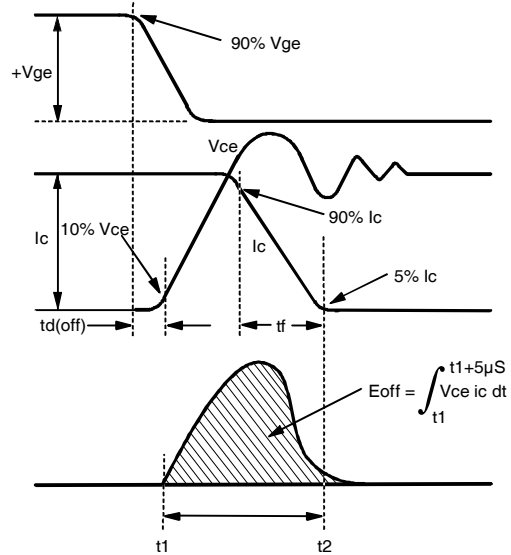


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

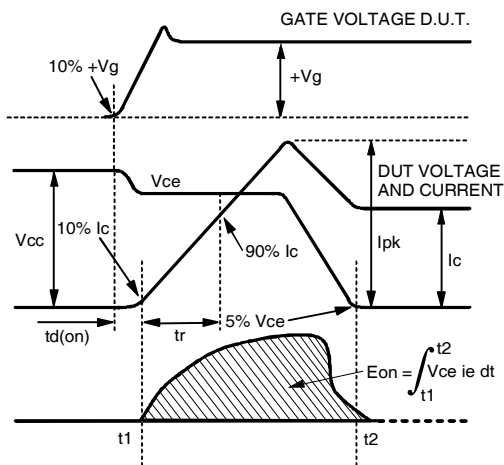


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

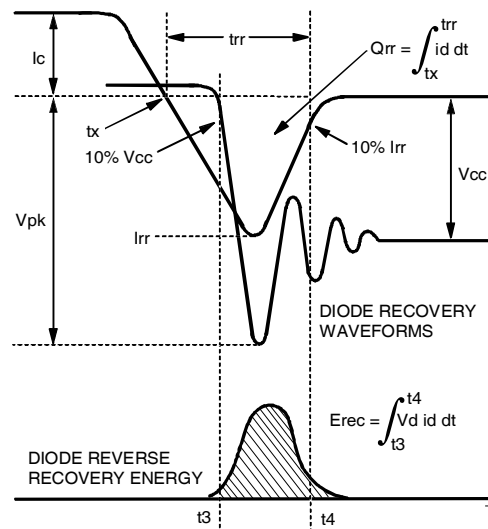


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

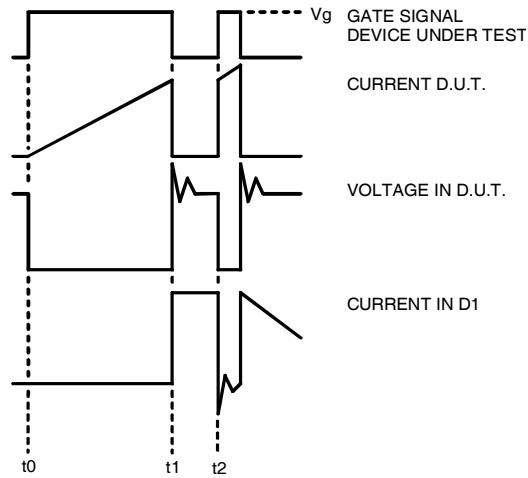


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

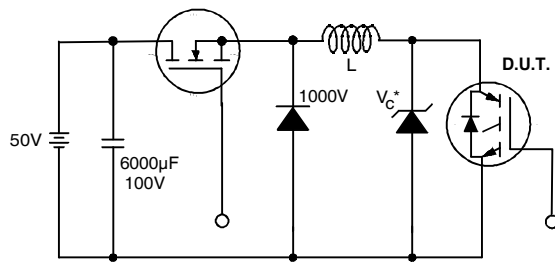
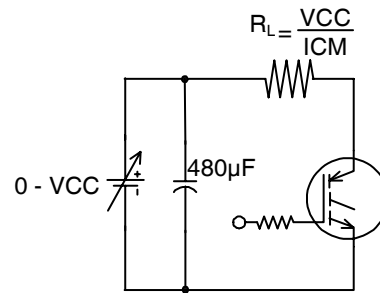


Figure 19. Clamped Inductive Load Test Circuit



Pulsed Collector Current Test Circuit

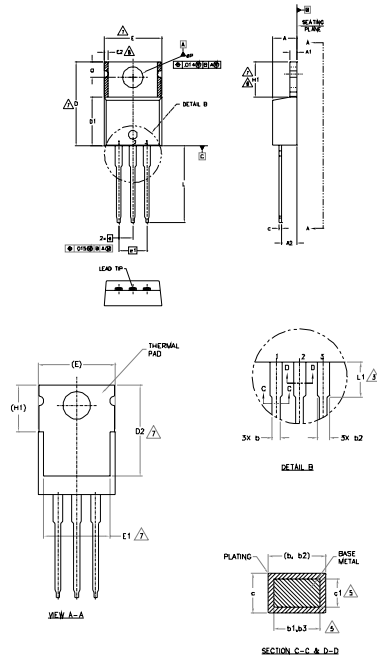
Figure 20. Pulsed Collector Current Test Circuit

IRG4BC30UDPbF

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 23\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



- NOTES:
- 1- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M-1994.
 - 2- DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS)
 - 3- LEAD DIMENSION AND FINISH UNCONTROLLED IN 1:1.
 - 4- DIMENSION D, DI & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 5- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
 - 6- CONTROLLING DIMENSION - INCHES.
 - 7- THERMAL PAD CONTOURS OPTIONAL WITHIN DIMENSIONS E1, D2 & E1.
 - 8- DIMENSION E2 x H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
 - 9- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	5
b1	0.38	0.91	.015	.036	
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.26	0.56	.014	.022	5
D	14.22	16.61	.560	.650	4
D1	8.38	9.02	.330	.355	7
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4, 7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	0.30	8
e	2.54 BSC	-	.100 BSC	-	
e1	2.54 BSC	-	.100 BSC	-	
H1	5.84	6.86	.230	.270	7, 8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
MP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

- 1- GATE
- 2- DRN
- 3- SOURCE

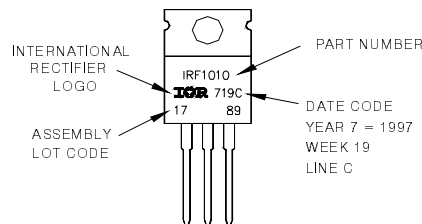
SEMI CONDUCTOR

- 1- GATE
- 2- COLLECTOR
- 3- EMITTER

- 1- ANODE
- 2- CATHODE
- 3- ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE 'C'
Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.